

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
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EPAS ID: PAT5468202

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
CRYSTAL SOLAR, INC.	01/30/2019
RECEIVING PARTY DATA	
Name:	STELLAR TECHNIK INC.
Street Address:	3050 CORONADO DRIVE
City:	SANTA CLARA
State/Country:	CALIFORNIA
Postal Code:	95054
PROPERTY NUMBERS Total: 38	
Property Type	Number
Patent Number:	9455360
Patent Number:	8298629
Patent Number:	8663753
Patent Number:	8673081
Patent Number:	9556522
Patent Number:	9920451
Patent Number:	8030119
Patent Number:	8481357
Patent Number:	8900399
Patent Number:	8809097
Patent Number:	8609451
Patent Number:	9255346
Patent Number:	9397239
Patent Number:	9257284
Application Number:	15014404
Application Number:	15175000
Application Number:	15183728
Application Number:	15204979
Application Number:	15630277
Application Number:	15831139

Property Type	Number
Application Number:	15831146
PCT Number:	US1738717
PCT Number:	US1650016
PCT Number:	US1641404
PCT Number:	US0901457
PCT Number:	US1025449
PCT Number:	US1239900
PCT Number:	US1133792
PCT Number:	US1229708
PCT Number:	US1147486
PCT Number:	US1321439
PCT Number:	US1450792
PCT Number:	US1535698
PCT Number:	US1249648
PCT Number:	US1048058
PCT Number:	US0905855
PCT Number:	US0905852
PCT Number:	US1424925

CORRESPONDENCE DATA

Fax Number: (650)233-4545

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Email: desiree.ortiz@pillsburylaw.com

Correspondent Name: PILLSBURY WINTHROP SHAW PITTMAN LLP

Address Line 1: P.O. BOX 10500

Address Line 4: MCLEAN, VIRGINIA 22102

ATTORNEY DOCKET NUMBER:	016265-0000002
NAME OF SUBMITTER:	DESIREE ORTIZ
SIGNATURE:	/desireeortiz/
DATE SIGNED:	04/10/2019

Total Attachments: 13

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INTELLECTUAL PROPERTY ASSIGNMENT AGREEMENT

This INTELLECTUAL PROPERTY ASSIGNMENT AGREEMENT (this "IP Assignment"), dated as of January 30, 2019, is made by Crystal Solar Inc. ("Seller"), a Delaware corporation, located at 3050 Coronado Drive, Santa Clara, CA 95054, in favor of Stellar Technik Inc. ("Buyer"), a Delaware corporation, located at 3050 Coronado Drive, Santa Clara, CA 95054, the purchaser of certain assets of Seller pursuant to an Asset Purchase Agreement between Buyer and Seller, dated as of January 30, 2019 (the "Asset Purchase Agreement").

WHEREAS, under the terms of the Asset Purchase Agreement, Seller has conveyed, transferred, and assigned to Buyer, among other assets, all intellectual property of Seller, and has agreed to execute and deliver this IP Assignment, for recording with the United States Patent and Trademark Office, and corresponding entities or agencies in any applicable jurisdictions.

NOW THEREFORE, the parties agree as follows:

1. Assignment. For good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, Seller hereby irrevocably conveys, transfers, and assigns to Buyer, and Buyer hereby accepts, any and all of Seller's right, title, and interest in, arising out of, or associated with any of the following in any jurisdiction throughout the world (the "Assigned IP"):

(a) (i) issued patents and patent applications (whether provisional or non-provisional) that claim priority to a patent or patent application listed Schedule 1 or that claims priority from any patent or patent application from which a patent or patent application listed Schedule 1, claims priority, including divisionals, continuations, continuations-in-part, renewals, amendments, substitutions, reissues, reexaminations, extensions, or restorations of any of the foregoing, and other Governmental Authority-issued indicia of invention ownership (including certificates of invention, petty patents, and patent utility models) ("Patents"); (ii) trademarks, service marks, brands, certification marks, logos, trade dress, trade names, and other similar indicia of source or origin, together with the goodwill connected with the use of and symbolized by, and all registrations, applications for registration, and renewals of, any of the foregoing ("Trademarks"); (iii) copyrights and works of authorship, whether or not copyrightable, and all registrations, applications for registration, and renewals of any of the foregoing ("Copyrights"); (iv) internet domain names and social media account or user names (including "handles"), whether or not Trademarks, all associated web addresses, URLs, websites and web pages, social media accounts and pages, and all content and data thereon or relating thereto, whether or not Copyrights; (v) mask works, and all registrations, applications for registration, and renewals thereof; (vi) industrial designs, and all Patents, registrations, applications for registration, and renewals thereof; (vii) trade secrets, know-how, inventions (whether or not patentable), discoveries, improvements, technology, business and technical information, databases, data compilations and collections, tools, methods, processes, techniques, and other confidential and proprietary information and all rights therein ("Trade Secrets"); (viii) computer programs, operating systems, applications, firmware and other code, including all source code, object code, application programming interfaces, data files, databases,

protocols, specifications, and other documentation thereof ("Software"); (ix) rights of publicity; (x) any developed intellectual property that can be adapted and applied to silicon, non-silicon, solar, non-solar and any other product development; and (xi) all other intellectual or industrial property and proprietary rights.

(b) all licenses, sublicenses, consent to use agreements, settlements, coexistence agreements, covenants not to sue, waivers, releases, permissions and other contracts, whether written or oral, which Seller is a party, beneficiary or otherwise bound, relating to any of the foregoing, including without limitation all confidential information and invention assignment agreements with current and former employees and/or consultants.

(c) all rights of any kind whatsoever of Seller accruing under any of the foregoing provided by applicable law of any jurisdiction, by international treaties and conventions, and otherwise throughout the world;

(d) any and all royalties, fees, income, payments, and other proceeds now or hereafter due or payable with respect to any and all of the foregoing; and

(e) any and all claims and causes of action with respect to any of the foregoing, whether accruing before, on, or after the date hereof, including all rights to and claims for damages, restitution, and injunctive and other legal and equitable relief for past, present, and future infringement, dilution, misappropriation, violation, misuse, breach, or default, with the right but no obligation to sue for such legal and equitable relief and to collect, or otherwise recover, any such damages.

2. Recordation and Further Actions. Seller hereby authorizes the Commissioner for Patents in the United States Patent and Trademark Office, and the officials of corresponding entities or agencies in any applicable jurisdictions to record and register this IP Assignment upon request by Buyer. Following the date hereof, upon Buyer's reasonable request, and at Buyer's sole cost and expense, Seller shall take such steps and actions, and provide such cooperation and assistance to Buyer and its successors, assigns, and legal representatives, including the execution and delivery of any affidavits, declarations, oaths, exhibits, assignments, powers of attorney, or other documents, as may be reasonably necessary to effect, evidence, or perfect the assignment of the Assigned IP to Buyer, or any assignee or successor thereto.

3. Terms of the Asset Purchase Agreement. The parties hereto acknowledge and agree that this IP Assignment is entered into pursuant to the Asset Purchase Agreement, to which reference is made for a further statement of the rights and obligations of Seller and Buyer with respect to the Assigned IP. The representations, warranties, covenants, agreements, and indemnities contained in the Asset Purchase Agreement shall not be superseded hereby but shall remain in full force and effect to the full extent provided therein. In the event of any conflict or inconsistency between the terms of the Asset Purchase Agreement and the terms hereof, the terms of the Asset Purchase Agreement shall govern.

4. Counterparts. This IP Assignment may be executed in counterparts, each of which shall be deemed an original, but all of which together shall be deemed one and the same agreement.

A signed copy of this IP Assignment delivered by facsimile, e-mail, or other means of electronic transmission shall be deemed to have the same legal effect as delivery of an original signed copy of this IP Assignment.


5. Successors and Assigns. This IP Assignment shall be binding upon and shall inure to the benefit of the parties hereto and their respective successors and assigns.

6. Governing Law. This IP Assignment shall be governed by and construed in accordance with the internal laws of the State of Delaware without giving effect to any choice or conflict of law provision or rule (whether of the State of Delaware or any other jurisdiction).

[signature page to follow]

IN WITNESS WHEREOF, Seller has duly executed and delivered this IP Assignment as of the date first above written.

Crystal Solar Inc.

By: 
Name: T.S.R. Ar
Title: CEO
Address for Notices:
3050 Coronado Drive
Santa Clara, CA 95054
Attention:
Email:

A notary public or other officer completing this certificate verifies only the identity of the individual who signed the document to which this certificate is attached, and not the truthfulness, accuracy, or validity of that document.

State of California)
County of _____)

On _____ before me, _____, personally appeared _____, who proved to me on the basis of satisfactory evidence to be the person(s) whose name(s) is/are subscribed to the within instrument and acknowledged to me that he/she/they executed the same in his/her/their authorized capacity(ies), and that by his/her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

WITNESS my hand and official seal.

Signature _____
Signature of Notary Public

AGREED TO AND ACCEPTED:

Stellar Technik Inc.

By: 

Name: NITENDRA R. TANTI

Title:

Address for Notices: 3050 - CORONADO DRIVE,
SANTA CLARA, CA 95054

Attention:

Email:

SCHEDULE 1
ASSIGNED PATENTS

Client Ref.	Patent No.	Title	Issue Date	Pub. No. And Pub. Date
Issued U.S. Patents				
CRY-002C	9,455,360 Serial No. 14/536,125 Filed 11/07/2014 Continuation of 13/208,302 Filed 08/11/2011, now US Pat. 8,883,552, which claims benefit of U.S. Prov. Serial No. 61/401,400 Filed 08/11/2010.	MWT ARCHITECTURE FOR THIN SI SOLAR CELLS	09/27/2016	US2015-0187966 07/02/2015
CRY-005	8,298,629 Serial No. 12/392,448 filed 02/25/2009	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	10/30/2012	US2010-0215872 08/26/2010
CRY-005 (CON)	8,663,753 Serial No. 13/664,332 filed 10/30/2012 CON of U.S. Serial No. 12/392,448, filed 02/25/09.	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	03/04/2014	US2013-0059430 03/07/2013
CRY-005(CIP)	8,673,081 Serial No. 12/713,116 filed 02/25/2010 CIP of U.S. Serial No. 12/392,448, filed 02/25/09.	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	3/18/2014	US2010-0263587 10/21/2010
CRY-005C2	9,556,522 Serial No. 14/196,609 Filed 03/04/2014 Continuation of 13/664,332 now US 8,663,753 which is a continuation of 12/392,448, now US 8,298,629	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	01/31/2017	US2014-295106 10/02/2014
CRY-005-CIP-C	9,920,451 Serial No. 14/216,434 Filed 03/17/2014 Continuation of 12/713,116 now US 8,673,081 which is a CIP of 12/392,448 now US 8,298,629	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	03/20/2018	US2014-0311403 10/23/2014

Client Ref	Patent No.	Title	Issue Date	Pub. No. And Pub. Date
CRY-006	8,030,119 Serial No. 12/399,248 filed 03/06/2009	INTEGRATED METHOD AND SYSTEM FOR MANUFACTURING MONOLITHIC PANELS OF CRYSTALLINE SOLAR CELLS	10/04/2011	US 2009-0227063 09/10/2009
CRY-006- CIP	8,481,357 Serial No. 12/766,765 filed 4/23/2010 CIP of 12/399,248 which claims priority to 61/068,629 filed 03/08/2008	THIN FILM SOLAR CELL WITH CERAMIC HANDLING LAYER	07/9/2013	US 2011-0186117 08/04/2011
CRY-006 (DIV)	8,900,399 Serial No. 13/050,807 filed 03/17/2011 Divisional of U.S. Ser. No. 12/399,248 filed 03/06/09.	INTEGRATED METHOD AND SYSTEM FOR MANUFACTURING MONOLITHIC PANELS OF CRYSTALLINE SOLAR CELLS	12/02/2014	US2011-0300715 12/08/11
CRY-009	8,809,097 Serial No. 13/241,112 filed 09/22/2011 Claims priority to U.S. Prov. Serial No. 61/403,962 filed 09/22/10.	PASSIVATED EMITTER REAR LOCALLY PATTERNED EPITAXIAL SOLAR CELL	08/19/2014	
CRY-013	8,609,451 Serial No. 13/424,287 filed 03/19/2012	IN SITU EPITAXIAL DEPOSITION OF FRONT AND BACK P- N JUNCTIONS IN SINGLE CRYSTAL SILICON SOLAR CELLS	12/17/2013	US2012-0288990 11/15/2012
CRY-012	9,255,346 Serial No. 13/483,002 Filed 02/07/013 Claims priority to U.S. Prov. Serial No. 61/491,152 filed 05/27/11	SILICON WAFERS BY EPITAXIAL GROWTH	02/09/2016	US2013-0032084 02/07/2013

Client Ref.	Patent No.	Title	Issue Date	Pub. No. And Pub. Date
CRY-013C	9,397,239 Serial No. 14/109,422 Filed 12/17/2013	IN SITU EPITAXIAL DEPOSITION OF FRONT AND BACK P-N JUNCTIONS IN SINGLE CRYSTAL SILICON SOLAR CELLS	07/19/2016	US2014-0182673 07/03/2014
CRY-015	9,257,284 Serial No. 13/740,980 Filed 01/14/2013 Claims priority to U.S. Prov. Serial Nos. 61/656,957 filed 06/07/2012 and 61/586,701 filed 01/13/2012	SILICON HETEROJUNCTION SOLAR CELLS	02/09/2016	US2013-0180578 07/18/2013
U.S. Utility Applications				
CRY-012C	15/014,404 Con. of U.S. Patent Application Serial No. 13/483,002 filed May 29, 2012, which claims the benefit of U.S. Provisional Application No. 61/491,152 filed May 27, 2011.	SILICON WAFERS BY EPITAXIAL DEPOSITION	02/03/2016	US2016-0222544 08/04/2016
CRY-025	15/175,000 Claims priority to U.S. Prov. Serial Nos. 62/171,202 filed 06/4/2015, and 62/213/087 filed 09/01/2015.	CVD REACTOR CHAMBER WITH RESISTIVE HEATING AND SUBSTRATE HOLDER	06/06/2016	US 2017-0037514 02/09/2017
CRY-022	15/183,728 Claims priority to U.S. Prov. Serial No. 62/175,986 filed 06/15/2015	HIGH EFFICIENCY SINGLE CRYSTAL SILICON SOLAR CELL WITH EPITAXIALLY DEPOSITED P-TYPE SILICON DEVICE LAYERS INCLUDING A MODERATELY DOPED P-TYPE SILICON BSF LAYER	06/15/2016	Non-publication requested
CRY-024	15/204,979 Claims priority to U.S. Prov. Serial No. 62/189,643 filed 07/07/2015.	HIGH EFFICIENCY SINGLE CRYSTAL SILICON SOLAR CELL WITH EPITAXIALLY DEPOSITED SILICON LAYERS WITH DEEP JUNCTION(S)	07/07/2016	US 2017-0012149 01/12/2017

Client Ref.	Patent No.	Title	Issue Date	Pub. No. And Pub. Date
CRY-026	15/630,277 Claims priority to U.S. Prov. Ser. No. 62/354,663 filed 06/24/2016.	SEMICONDUCTOR LAYER SEPARATION FROM SINGLE CRYSTAL SILICON SUBSTRATE BY INFRARED IRRADIATION OF POROUS SILICON SEPARATION LAYER	06/22/2017	US2017-0372966 12/28/2017
CRY-029	15/831,139 Claims priority to U.S. Prov. Ser. No. 62/429,674 filed 12/02/2016	CVD REACTOR CHAMBER WITH RESISTIVE HEATING FOR SILICON CARBIDE DEPOSITION	12/04/2017	
CRY-030	15/831,146 Claims priority to U.S. Prov. Ser. No. 62/429,689 filed 12/02/16	PROCESS CHAMBER WITH RESISTIVE HEATING	12/04/2017	
PCT Applications				
CRY-026 (PCT)	PCT/US17/38717 Claims priority to U.S. Prov. Ser. No. 62/354,663 filed 06/24/2016.	SEMICONDUCTOR LAYER SEPARATION FROM SINGLE CRYSTAL SILICON SUBSTRATE BY INFRARED IRRADIATION OF POROUS SILICON SEPARATION LAYER	06/22/2017 (PCT filing date)	WO 2017/223296 12/28/2017
	PCT/US16/50016 Claims priority to U.S. Prov. Ser. No. 62/213,087 filed 09/01/2015.	CVD REACTOR CHAMBER WITH RESISTIVE HEATING AND SUBSTRATE HOLDER	09/01/2016 (PCT filing date)	WO 2017/040868 03/09/2017
	PCT/US16/41404 Claims priority to U.S. Prov. Ser. No. 62/189,643 filed 07/07/2015.	HIGH EFFICIENCY SINGLE CRYSTAL SILICON SOLAR CELL WITH EPITAXIALLY DEPOSITED SILICON LAYERS WITH DEEP JUNCTION(S)	07/07/2016 (PCT filing date)	WO 2017/007972 01/12/2017

Client Ref.	Patent No.	Title	Issue Date	Pub. No. And Pub. Date
	PCT/US09/01457 Claims priority to U.S. Prov. Ser. No. 61/068,629 filed 03/08/2008.	INTEGRATED METHOD AND SYSTEM FOR MANUFACTURING MONOLITHIC PANELS OF CRYSTALLINE SOLAR CELLS	03/06/2009 (PCT filing date)	WO 2009/114108 09/17/2006
	PCT/US10/25449 Con. of U.S. Patent Application Serial No. 12/392,448 filed 02/25/2009, now US 8,673,081 issued 10/30/2012.	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	2/25/2009 (PCT filing date)	WO 2010/099344 09/02/2010
	PCT/US12/39900 Claims priority to U.S. Prov. Ser. No. 61/491,152 filed 05/27/2011.	SILICON WAFERS BY EPITAXIAL DEPOSITION	05/29/2012 (PCT filing date)	WO 2012/166748 12/06/2012
	PCT/US11/33792 Con. of U.S. Patent Application Serial No. 12/766,765 filed 04/23/2010, now US 8,481,357 issued 07/09/2013.	THIN FILM SOLAR CELL WITH CERAMIC HANDLING LAYER	04/25/2011 (PCT filing date)	WO 2011/133975 10/27/2011
	PCT/US12/29708 Claims priority to U.S. Prov. Ser. No. 61/454,363 filed 03/18/2011.	INSITU EPITAXIAL DEPOSITION OF FRONT AND BACK JUNCTIONS IN SINGLE CRYSTAL SILICON SOLAR CELLS	03/19/2012 (PCT filing date)	WO 2012/129184 09/27/2012
	PCT/US11/47486 Claims priority to U.S. Prov. Ser. No. 61/454,363 filed 03/18/2011, and to U.S. Prov. Ser. No. 61/401,400 filed 08/11/2010.	MWT ARCHITECTURE FOR THIN SI SOLAR CELLS	08/11/2011 (PCT filing date)	WO 2012/021750 02/16/2012
	PCT/US13/21439 Claims priority to U.S. Prov. Ser. No. 61/656,957 filed 06/07/2012, and to U.S. Prov. Ser. No. 61/586,701 filed 01/13/2012.	SILICON HETERO JUNCTION SOLAR CELLS	01/14/2013 (PCT filing date)	WO 2013/106827 07/18/2013
	PCT/US2014/050792 Claims priority to U.S. Prov. Ser. No. 61/922,469 filed 12/31/2013, and 61/865,100 filed 08/12/2013.	SILICON WAFERS WITH EPITAXIAL DEPOSITION P-N JUNCTIONS	08/12/2014 (PCT filing date)	WO 2015/023709 02/19/2015

Client Ref.	Patent No.	Title	Issue Date	Pub. No. And Pub. Date
	PCT/US2015/035698 Claims priority to U.S. Prov. Ser. No. 62/011,549 filed 06/12/2014.	CVD EPITAXIAL REACTOR CHAMBER WITH RESISTIVE HEATING, THREE CHANNEL SUBSTRATE CARRIER AND GAS PREHEAT STRUCTURE	06/12/2015 (PCT filing date)	WO 2015/192105 12/17/2015
	PCT/US2012/049648 Claims priority to U.S. Prov. Ser. No. 61/514,641 filed 08/03/2011, and 61/652,063 filed 05/25/2012.	PHOTOVOLTAIC MODULE FABRICATION WITH THIN SINGLE CRYSTAL EPITAXIAL SILICON DEVICES	08/03/2012 (PCT filing date)	WO 2013/020111 02/07/2013
	PCT/US2010/048058 Con. of U.S. Patent Application Serial No. 12/556,357 filed 09/09/2009.	METHOD FOR MANUFACTURING THIN CRYSTALLINE SOLAR CELLS PRE-ASSEMBLED ON A PANEL	09/08/2010 (PCT filing date)	WO 2011/031707 03/17/2011
	PCT/US2009/005855 Con. of U.S. Patent Application Serial No. 12/290,588 filed 10/31/2008.	THIN TWO SIDED SINGLE CRYSTAL SOLAR CELL AND MANUFACTURING PROCESS THEREOF	10/27/2009 (PCT filing date)	WO 2010/062343 06/03/2010
	PCT/US2009/005852 Con. of U.S. Patent Application Serial No. 12/290,582 filed 10/31/2008.	THIN INTERDIGITATED BACKSIDE CONTACT SOLAR CELL AND MANUFACTURING PROCESS THEREOF	10/27/2009 (PCT filing date)	WO 2010/062341 06/03/2010
	PCT/US2014/024925 Claims priority to U.S. Prov. Ser. No. 61/777,891 filed 03/12/2013, and 61/961,233 filed 10/07/2013.	LOW SHADING LOSS SOLAR MODULE	10/09/2014 (PCT filing date)	WO 2014/165238 10/09/2014
Foreign National Phase Registrations (Foreign Patents)				
CRY-005JP (JAPAN)	5600125 2011-552160 Based on International Patent Application PCT/US2010/025449. Earliest priority 02/25/2009	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	08/22/2014 02/25/2010 (PCT Date) National Phase Entry 08/25/2011	(See registration details in column 2.)

Client Ref.	Patent No.	Title	Issue Date	Pub. No. And Pub. Date
CRY-005JP (DIV) (JAPAN)	2014-165124 Divisional of 2011-552160 (now 5600125) Based on International Patent Application PCT/US2010/025449. Earliest priority 02/25/2009	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	5897081 03/11-2016 02/25/2010 (PCT Date) DIV Entry in JP 08/14/2014	(See registration details in column 2.)
CRY-005CN (CHINA)	ZL 201080018350.0 201080018350.0 Based on International Patent Application PCT/US2010/025449. Earliest Priority 02/25/2009	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	09/17/2014 02/25/2010 (PCT Date) National Phase Entry 10/21/2011	(See registration details in column 2.)
CRY-005CN (DIV) (CHINA)	201410407556.2 Divisional of ZL 201080018350.0 201080018350.0 Based on International Patent Application PCT/US2010/025449. Earliest Priority 02/25/2009	HIGH THROUGHPUT MULTI-WAFER EPITAXIAL REACTOR	02/25/2010 (PCT Date) DIV Entry in CN 08/19/2014	(See registration details in column 2.)
CRY-005KR (KOREA)	10-2011-7022204 Based on International Patent Application PCT/US2010/025449. Earliest priority 02/25/2009	High Throughput Multi- Wafer Epitaxial Reactor	10-1655261 09/01/2016 02/25/10 (PCT Date) National Phase Entry 09/22/2011	10-2011-0120963 11/04/2011
CRY-012CN-DIV (CHINA)	201610926004.1 Divisional of ZL201280037177.8 (now abandoned) PCT/US2012/039900 Earliest priority 05/27/2011	SILICON WAFERS BY EPITAXIAL DEPOSITION	05/29/2012 (PCT date) National Phase Entry Date 10/24/2016	CN 107022789 A 08/08/2017
CRY-012JP (JAPAN)	6097742 2014-513647 Based on International Patent Application PCT/US2012/039900 Earliest Priority 05/27/2011	SILICON WAFERS BY EPITAXIAL DEPOSITION	02/24/2017 05/29/2012 (PCT Date) National Phase Entry Date 11/27/2013	(See registration details in column 2.)

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Schedule 1 – 8

RECORDED: 04/10/2019

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